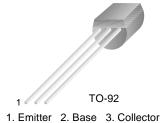


SS9014

Pre-Amplifier, Low Level & Low Noise

- High total power dissipation. (P_T=450mW)
- High h_{FE} and good linearity
- Complementary to SS9015



NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_a =25°C unless otherwise noted

| Symbol | Parameter | Ratings | Units | |
|------------------|-----------------------------|-----------|-------|--|
| V _{CBO} | Collector-Base Voltage | 50 | V | |
| V _{CEO} | Collector-Emitter Voltage | 45 | V | |
| V _{EBO} | Emitter-Base Voltage | 5 | V | |
| I _C | Collector Current | 100 | mA | |
| P _C | Collector Power Dissipation | 450 | mW | |
| T _J | Junction Temperature | 150 | °C | |
| T _{STG} | Storage Temperature | -55 ~ 150 | °C | |

Electrical Characteristics T_a=25°C unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Тур. | Max. | Units |
|-----------------------|-------------------------------------|---|------|------|------|-------|
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_C = 100 \mu A, I_E = 0$ | 50 | | | V |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 1 \text{mA}, I_B = 0$ | 45 | | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_E = 100 \mu A, I_C = 0$ | 5 | | | V |
| I _{CBO} | Collector Cut-off Current | $V_{CB} = 50 \text{V}, I_{E} = 0$ | | | 50 | nA |
| I _{EBO} | Emitter Cut-off Current | $V_{EB} = 5V$, $I_C = 0$ | | | 50 | nA |
| h _{FE} | DC Current Gain | $V_{CE} = 5V$, $I_{C} = 1mA$ | 60 | 280 | 1000 | |
| V _{CE} (sat) | Collector-Base Saturation Voltage | $I_C = 100 \text{mA}, I_B = 5 \text{mA}$ | | 0.14 | 0.3 | |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | $I_C = 100 \text{mA}, I_B = 5 \text{mA}$ | | 0.84 | 1.0 | V |
| V _{BE} (on) | Base-Emitter On Voltage | $V_{CE} = 5V$, $I_{C} = 2mA$ | 0.58 | 0.63 | 0.7 | V |
| C _{ob} | Output Capacitance | V _{CB} =10V, I _E =0 f=1MHz | | 2.2 | 3.5 | pF |
| f _T | Current Gain Bandwidth Product | $V_{CE} = 5V$, $I_{C} = 10mA$ | 150 | 270 | | MHz |
| NF | Noise Figure | V_{CE} =5V, I_{C} =0.2mA f=1KHz, R_{S} =2K Ω | | 0.9 | 10 | dB |

h_{FE} Classification

| Classification | Α | В | С | D |
|-----------------|----------|-----------|-----------|------------|
| h _{FE} | 60 ~ 150 | 100 ~ 300 | 200 ~ 600 | 400 ~ 1000 |

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Typical Characteristics

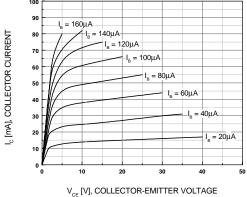


Figure 1. Static Characteristic



 $I_{\rm C} = 20 I_{\rm R}$

100

Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

 $I_{_{\rm C}}$ [mA], COLLECTOR CURRENT

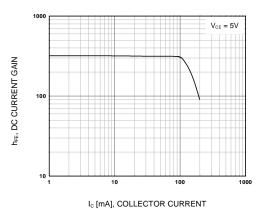


Figure 2. DC current Gain

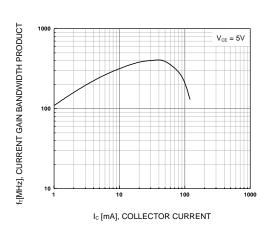
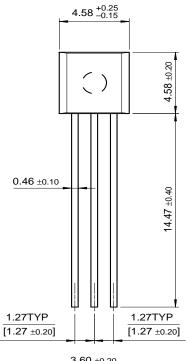


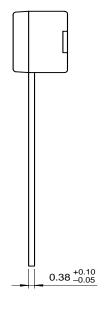
Figure 4. Current Gain Bandwidth Product

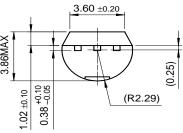
 $V_{\text{BE}}(\text{sat}), V_{\text{CE}}(\text{sat}) \text{[mV]}, \, \text{SATURATION VOLTAGE}$

Package Dimensions

TO-92







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